

**SEMICONDUCTOR DEVICE BONDING PAD RESISTANT TO  
STRESS AND METHOD OF FABRICATING THE SAME**

Abstract of the Disclosure

According to various embodiments of the present invention, a bonding pad structure of a semiconductor device reduces damage caused by thermo-mechanical stress in beam lead bonding. A method of fabricating an improved bonding pad structure is also provided. A polysilicon film plate is preferably formed between a bonding pad metal layer and a dielectric layer. The polysilicon film plate absorbs external thermo-mechanical stress and improves the durability of the bonding pad in a bond pull test (BPT). The bonding between the bonding pad metal layer and the dielectric layer is also improved. Other features and advantages are also provided.